

TITLE OF INVENTION: CLEANING SOLUTION, METHOD FOR
CLEANING SUBSTRATE, AND METHOD FOR FORMING METAL-
CONTAINING FILM

ABSTRACT

The present invention is a cleaning solution for a composition for forming a metal-containing film, the cleaning solution containing: (A) a solvent; and (B) an organic acid, where the solvent (A) contains at least one kind of a first solvent (A-1) having a normal boiling point of lower than 160°C and at least one kind of a second solvent (A-2) having a normal boiling point of 160°C or higher and lower than 500°C. This can provide: a cleaning solution excellent in cleaning property, such as the removal of the metal-containing film on the periphery of a substrate, hump suppression property, and waste liquid stability when a composition for forming a metal-containing film is applied to the substrate; a method for cleaning a semiconductor substrate, using the cleaning solution; and a method for forming a metal-containing film, using the cleaning method.

[FIG. 1(A)-1(C)]